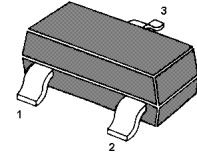
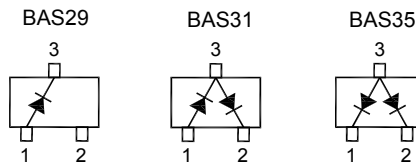


BAS29, BAS31, BAS35-AH

Silicon Epitaxial Planar Switching Diodes

Features

- AEC-Q101 Qualified and PPAP Capable
- Halogen and Antimony Free(HAF), RoHS compliant



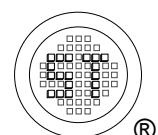
BAS29 Marking Code: **L20**
 BAS31 Marking Code: **L21**
 BAS35 Marking Code: **L22**
 SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

| Parameter | Symbol | Value | Unit |
|---|---|---------------|------------------|
| Repetitive Peak Reverse Voltage | V_{RRM} | 120 | V |
| Maximum Average Forward Current | $I_{F(AV)}$ | 200 | mA |
| Repetitive Peak Forward Current | I_{FRM} | 600 | mA |
| Non-Repetitive Peak Forward Surge Current | I_{FSM} | 2 1 | A |
| | $t = 1\ \mu\text{s}$ $t = 1\ \text{s}$ | | |
| Power Dissipation | P_{tot} | 350 | mW |
| Junction Temperature | T_j | 150 | $^\circ\text{C}$ |
| Storage Temperature Range | T_{stg} | - 55 to + 150 | $^\circ\text{C}$ |

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

| Parameter | Symbol | Min. | Max. | Unit |
|--|-------------|------|------|---------------|
| Forward Voltage | | | | |
| at $I_F = 10\ \text{mA}$ | V_F | - | 750 | mV |
| at $I_F = 50\ \text{mA}$ | V_F | - | 840 | mV |
| at $I_F = 100\ \text{mA}$ | V_F | - | 900 | mV |
| at $I_F = 200\ \text{mA}$ | V_F | - | 1 | V |
| at $I_F = 400\ \text{mA}$ | V_F | - | 1.25 | V |
| Reverse Current | | | | |
| at $V_R = 90\ \text{V}$ | I_R | - | 100 | nA |
| at $V_R = 90\ \text{V}, T_J = 150\text{ }^\circ\text{C}$ | I_R | - | 100 | μA |
| Reverse Breakdown Voltage | $V_{(BR)R}$ | 120 | - | V |
| at $I_R = 1\ \text{mA}$ | | | | |
| Total Capacitance | C_T | - | 35 | pF |
| at $V_R = 0\ \text{V}, f = 1\ \text{MHz}$ | | | | |
| Reverse Recovery Time | t_{rr} | - | 50 | ns |
| at $I_F = I_R = 10\ \text{mA}, I_{rr} = 1\ \text{mA}, R_L = 100\ \Omega$ | | | | |



BAS29, BAS31, BAS35-AH

